INFORMATION DISCLOSURE CITATION PTO-1449	Customer Number 26615	ATTORNEY'S DKT NO. H1417D	DIVISIONAL APPLICATION OF APPLICATION SERIAL NO. ~~10/405,343~~ 10/825175
		APPLICANT(S) Ming-Ren Lin et al.	
		FILING DATE APRIL 16, 2004	GROUP ~~Unassigned~~ 2813

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EXAMINER	DATE CONSIDERED 9/27/04

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).

INFORMATION DISCLOSURE CITATION PTO-1449	Customer Number 26615	ATTORNEY'S DKT NO. H1417D	DIVISIONAL APPLICATION OF APPLICATION SERIAL NO. ~~10/405,343~~
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

DS	Co-pending U.S. Application Serial No. 10/754,515 and Preliminary Amendment, filed January 12, 2004 titled "FinFET Device With Multiple Fin Structures."
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EXAMINER	DATE CONSIDERED
DS	9/27/04

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